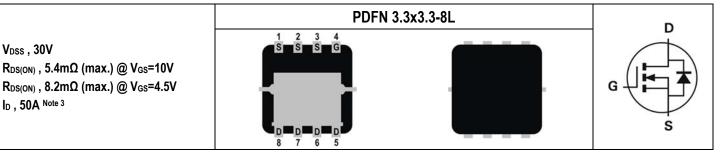


SG30N04E

30V N-Channel Power MOSFET



Description	Features
The SG30N04E uses advanced Trench technology and designs to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	 Low On-Resistance Low Input Capacitance Low Miller Charge Low Input / Output Leakage Pb-free lead plating; RoHS compliant
	Applications
	 Motor / Body Load Control Load Switch DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG30N04E	Halogen-Free	PDFN 3.3x3.3-8L	E	Tape & Reel	5,000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	30	V
Gate-Source Voltage		V _{GS}	±20	V
Drain Current Continuous	Tc=25°C		50	А
Drain Current-Continuous	T _c =100°C	lD ID	30	А
Drain Current-Pulsed Note 1		I _{DM}	150	А
Drain Current-Continuous Note 3	T _A =25°C		15	А
Drain Current-Continuous new o	T _A =70°C		12	А
Avalanche Current		las	50	А
Avalanche Energy, L=0.1mH		Eas	125	mJ
	T _c =25°C		59	W
Maximum Dawar Dissinction	Tc=100°C	D	23	W
Maximum Power Dissipation	T _A =25°C	PD PD	2	W
	T _A =70°C		0.8	W
Storage Temperature Range		Tstg	-55 to +175	°C
Operating Junction Temperature Range		TJ	-55 to +175	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	Reja	Steady State	-	-	62	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	2.1	°C/W



Electrical Characteristics (T_=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250µA	30	-	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =24V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage	lgss	$V_{GS}=\pm 20V$, $V_{DS}=0V$	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250µA	1.2	-	2.5	V
Drain-Source On-State Resistance	D	V _{GS} =10V, I _{DS} =20A	-	-	5.4	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _{DS} =10A	-	-	8.2	11122

DYNAMIC CHARACTERISTICS

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	2249	-	
Output Capacitance	Coss	V_{DS} =15V, V_{GS} =0V, f=1MHz	-	261	-	pF
Reverse Transfer Capacitance	Crss		-	205	-	
Gate Resistance	Rg	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	1.7	-	Ω

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	7.6	-	
Rise Time	tr	V _{DD} =15V, I _D =10A, V _{Gs} =10V,	-	14	-]
Turn-Off Delay Time	T _{d(off)}	Rg=3.3Ω	-	36.5	-	ns
Fall Time	t _f		-	10.3	-	
Total Gate Charge	Qg		-	19.6	-	
Gate to Source Gate Charge	Qgs	V _{DS} =15V, I _{DS} =10A, V _{GS} =4.5V	-	7.4	-	nC
Gate to Drain "Miller" Charge	Q _{gd}]	-	7	-	1

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Body-Diode Continuous Current	ls	V _G =V _D =0V, Force Current	-	-	40	Α
Pulsed Source Current	lsм	V _G =V _D =0V, Force Current	-	-	140	Α
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =1A	-	0.8	1.2	V
Body Diode Reverse Recovery Time	trr	V _{DD} =15V, I _F =20A, di/dt=100A/µs	-	13	-	ns
Body Diode Reverse Recovery Charge	Qrr	V _{DD} =15V, I _F =20A, di/dt=100A/µs	-	4	-	nC

Notes:

1. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

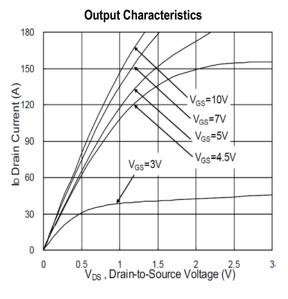
 R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0JC} is guaranteed by design while R_{0CA} is determined by the user's board design. R_{0JA} shown below for single device operation on FR-4 in still air.

3. The maximum current rating is limited by package.

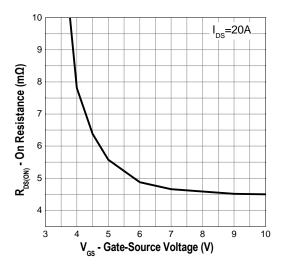


SG30N04E 30V N-Channel Power MOSFET

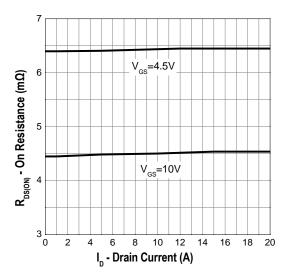
Typical Operating Characteristics



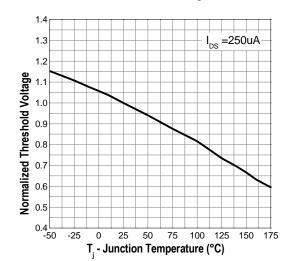
Gate-Source On Resistance



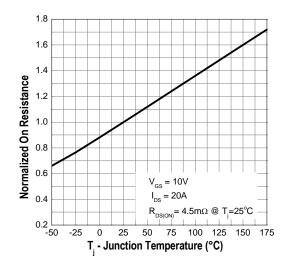
Drain-Source On Resistance



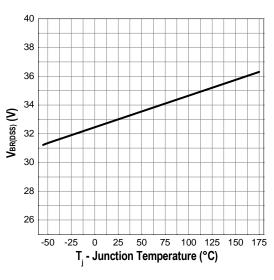
Gate Threshold Voltage



Drain-Source On Resistance



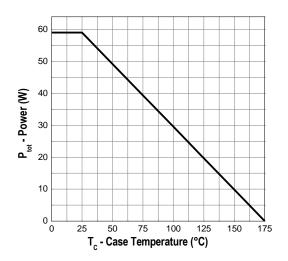
Drain-source Breakdown Voltage



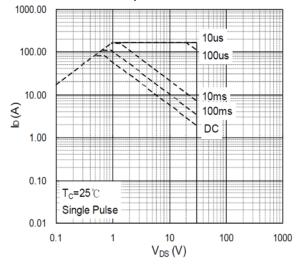


Typical Operating Characteristics (Cont.)

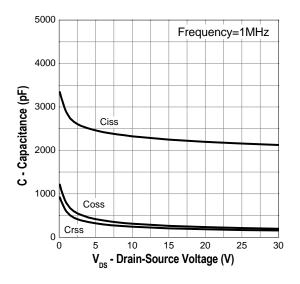
Power Dissipation

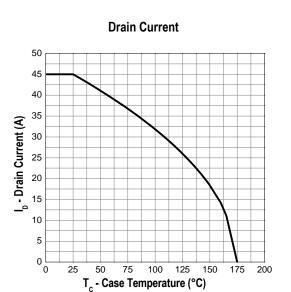


Safe Operation Area



Capacitance

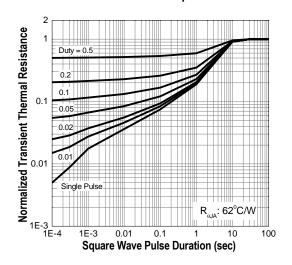




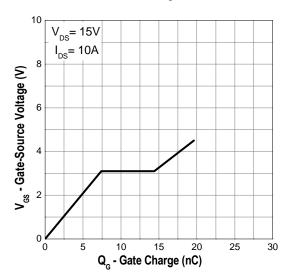
SG30N04E

30V N-Channel Power MOSFET

Transient Thermal Impedance



Gate Charge







Marking Information

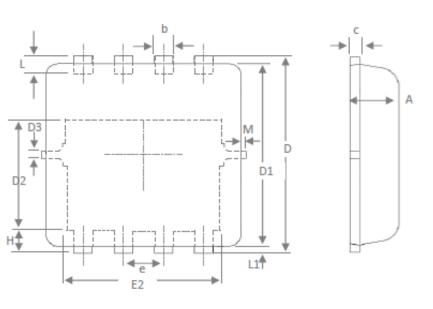
PDFN 3.3x3.3-8L (E)	Marking Rule
Laser Marking	Line 1 : Device
	30N04E
ومصفقه	Line 2 : Date Code
30N04E	YMMXXX
YMMXXX	Y:Year Code
•	MM : Month Code
	XXX : Serial Number
Diagram	Year Code Description As Below

Year Code Description

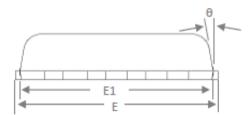
Year Code	Year				
0	2010	2020			
1	2011	2021			
2	2012	2022			
3	2013	2023			
4	2014	2024			
5	2015	2025			
6	2016	2026			
7	2017	2027			
8	2018	2028			
9	2019	2029			



Package of Dimension



Symbol	Min	Nor	Max
Α	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.00	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
е		0.65BSC	
Η	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
θ	-	10°	12°
М	-	-	0.15



Note:

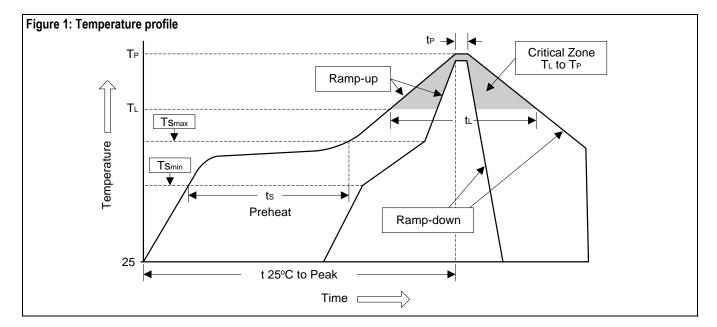
- 1. All Dimension Are In mm.
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.

SG30N04E 30V N-Channel Power MOSFET



Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t⊳)	10 10 300 300	2010 40 300
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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